

Arnab Hazari

List of Publications by Year in descending order

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26
papers

674
citations

933264

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h-index

794469

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27
all docs

27
docs citations

27
times ranked

994
citing authors

#	ARTICLE	IF	CITATIONS
1	Monolithic Electrically Injected Nanowire Array Edge-Emitting Laser on (001) Silicon. Nano Letters, 2014, 14, 4535-4541.	4.5	177
2	Room Temperature Electrically Injected Polariton Laser. Physical Review Letters, 2014, 112, 236802.	2.9	173
3	Electrically pumped single-photon emission at room temperature from a single InGaN/GaN quantum dot. Applied Physics Letters, 2014, 105, .	1.5	83
4	Formation and Nature of InGaN Quantum Dots in GaN Nanowires. Nano Letters, 2015, 15, 1647-1653.	4.5	58
5	III-nitride disk-in-nanowire 1.2×10^4 m monolithic diode laser on (001) silicon. Applied Physics Letters, 2015, 107, .	1.5	37
6	High performance red-emitting multiple layer InGaN/GaN quantum dot lasers. Japanese Journal of Applied Physics, 2016, 55, 032101.	0.8	30
7	Small signal modulation characteristics of red-emitting ($\lambda = 610$ nm) III-nitride nanowire array lasers on (001) silicon. Applied Physics Letters, 2015, 106, .	1.5	29
8	$1.3\text{-}\mu\text{m}$ Optical Interconnect on Silicon: A Monolithic III-Nitride Nanowire Photonic Integrated Circuit. IEEE Journal of Quantum Electronics, 2017, 53, 1-9.	1.0	23
9	An InN/InGaN/GaN nanowire array guided wave photodiode on silicon. Applied Physics Letters, 2016, 109, 191102.	1.5	13
10	Red and Near-Infrared III-Nitride Quantum Dot Lasers. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-9.	1.9	12
11	Finite-difference time-domain analysis of the tunability of Anderson localization of light in self-organized GaN nanowire arrays. Journal of Applied Physics, 2019, 125, 043104.	1.1	10
12	Optical constants of $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 \leq x \leq 0.73$) in the visible and near-infrared wavelength regimes. Optics Letters, 2015, 40, 3304.	1.7	9
13	III-Nitride Electrically Pumped Visible and Near-Infrared Nanowire Lasers on (001) Silicon. Semiconductors and Semimetals, 2017, 96, 385-409.	0.4	7
14	Bhattacharya et al. Reply. Physical Review Letters, 2016, 117, 029702.	2.9	4
15	Formation and properties of InGaN QDs: Influence of substrates. Applied Physics Letters, 2019, 114, .	1.5	3
16	InGaN/GaN dot-in-nanowire monolithic LEDs and lasers on (001) silicon. Proceedings of SPIE, 2017, , .	0.8	2
17	Infrared Absorption at 300 K in InGaN/GaN Disk-in-Nanowire Arrays Grown on (001) Silicon. IEEE Photonics Technology Letters, 2017, 29, 1751-1754.	1.3	2
18	Shape Evolution of Highly Lattice-Mismatched InN/InGaN Nanowire Heterostructures. Journal of Electronic Materials, 2018, 47, 966-972.	1.0	1

#	ARTICLE	IF	CITATIONS
19	Modeling photocurrent spectra of high-indium-content InGa _N disk-in-wire photodiode on silicon substrate. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2022, 144, 115371.	1.3	1
20	0.5-1.3 μ m III-nitride lasers and light emitting diodes epitaxially grown on (001) silicon. , 2015, , .		0
21	High performance InGa _N /(In)Ga _N quantum dot (λ =630 nm) lasers. , 2015, , .		0
22	III-nitride nanowire array edge-emitting 1.3 μ m diode laser on (001) silicon substrate. , 2016, , .		0
23	Monolithic III-nitride nanowire detectors on silicon. , 2016, , .		0
24	1.3 μ m III-nitride nanowire monolithic diode lasers and photonic integrated circuits on (001) silicon. , 2017, , .		0
25	III-nitride nanowire array based 1.3 μ m monolithic photonic integrated circuit on (001) silicon substrate. , 2017, , .		0
26	Modeling Photocurrent Spectra of High-Indium-Content InN/InGa _N Disk-in-Wire Photodiodes. , 2021, , .		0